

Fig. 1

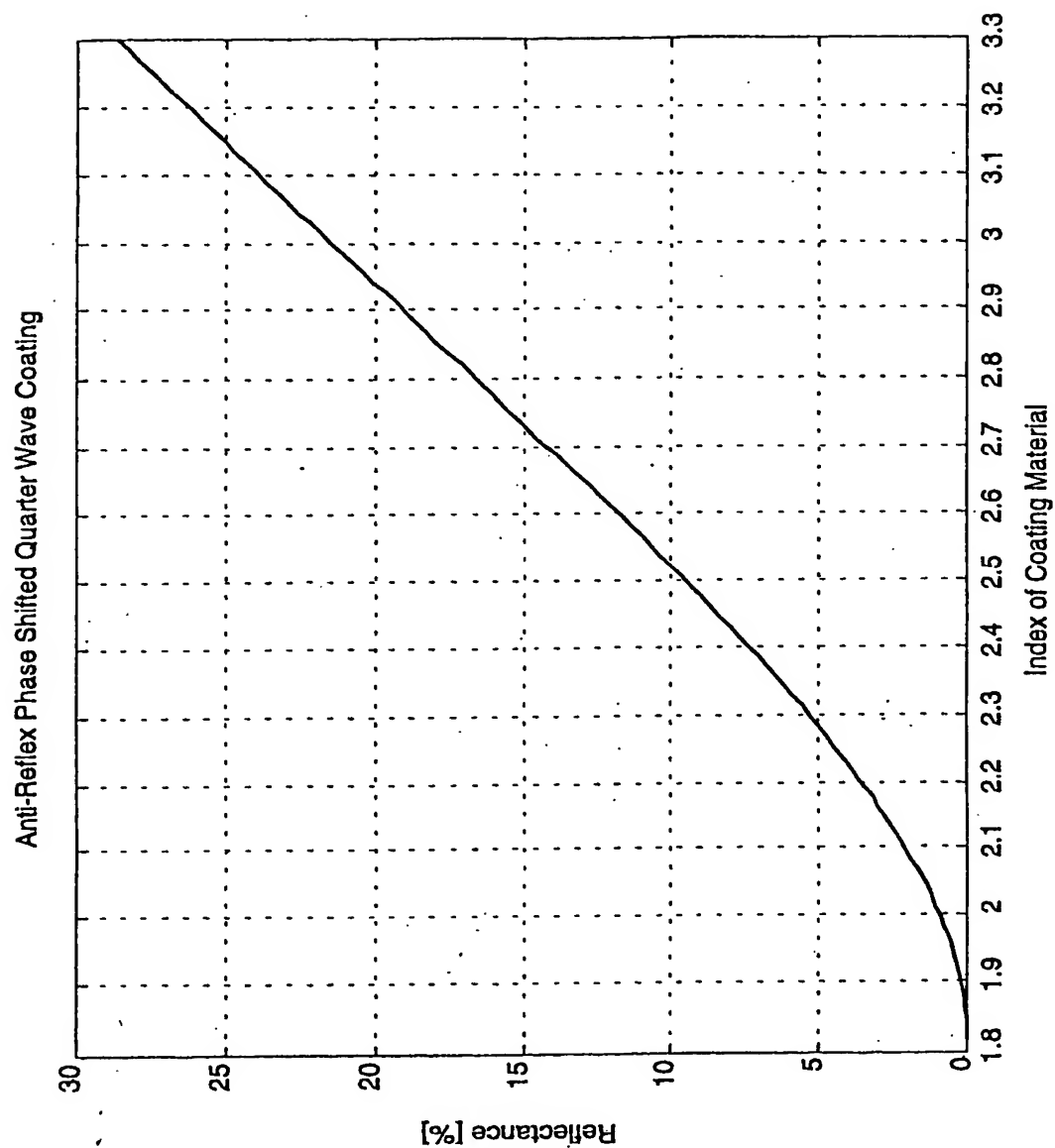
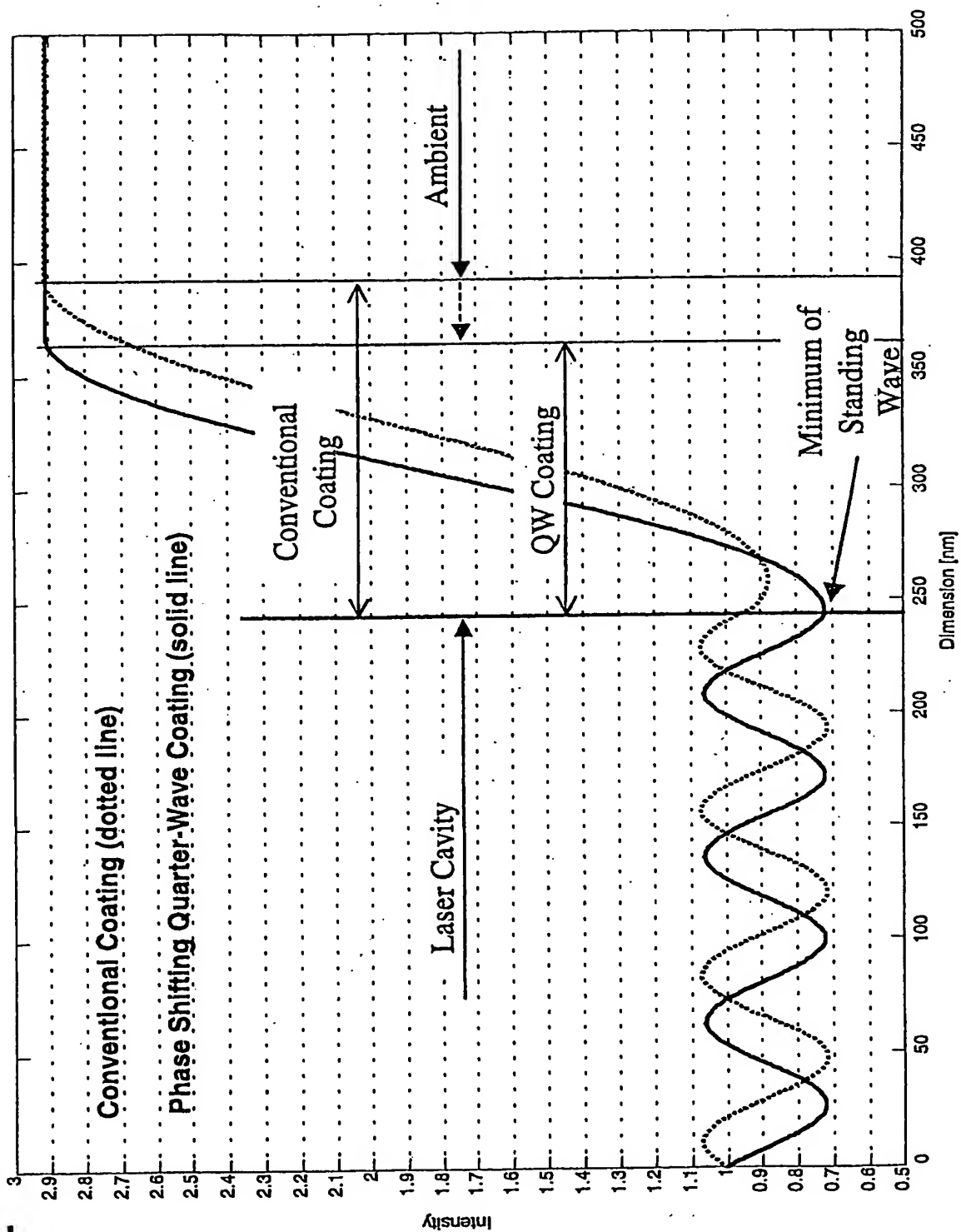
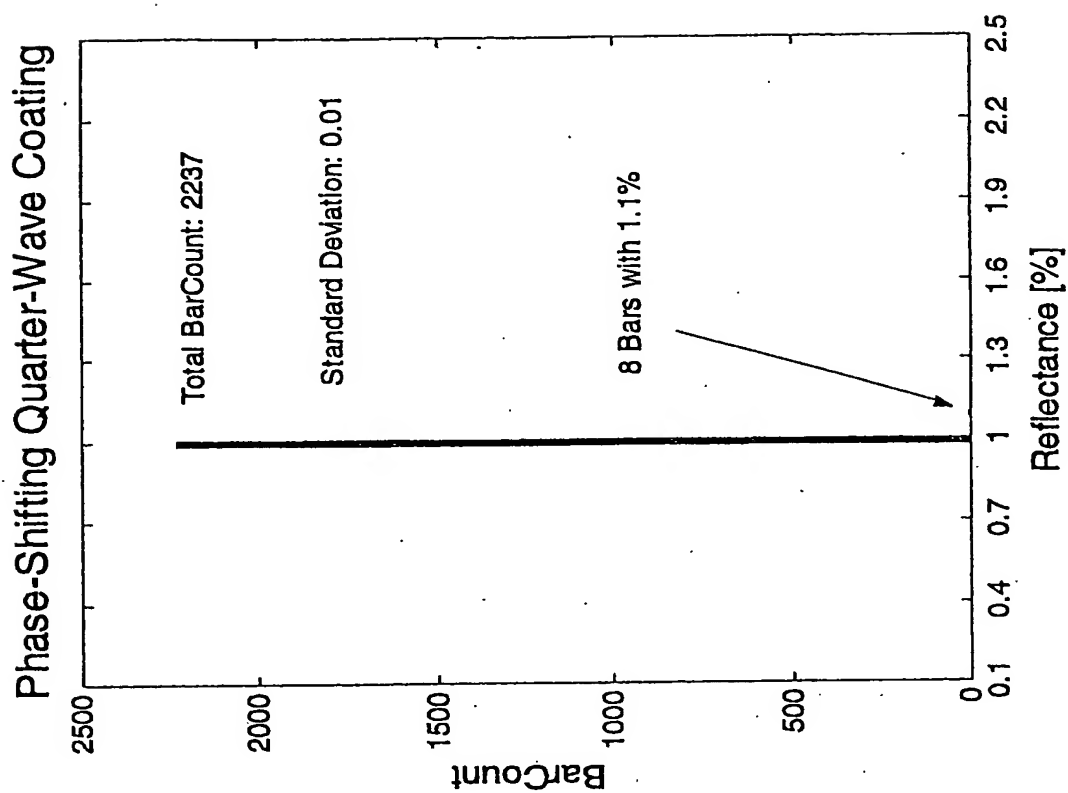


Fig. 2

Fig. 3



*Fig. 4(b)*



*Fig. 4(a)*

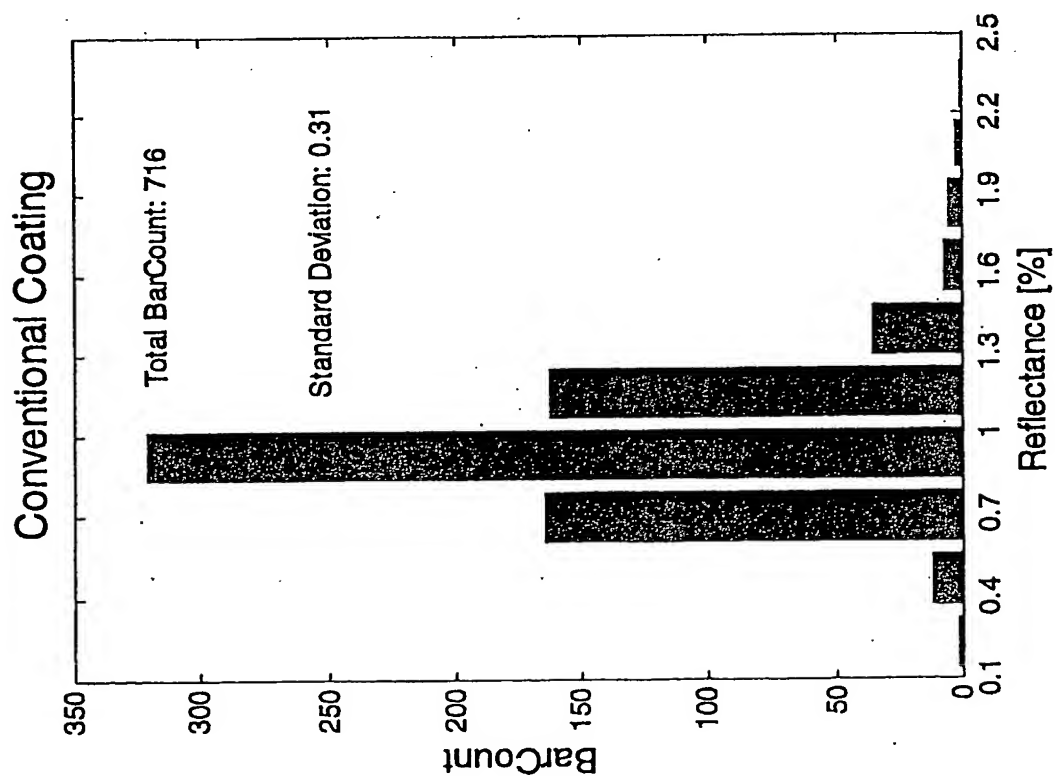
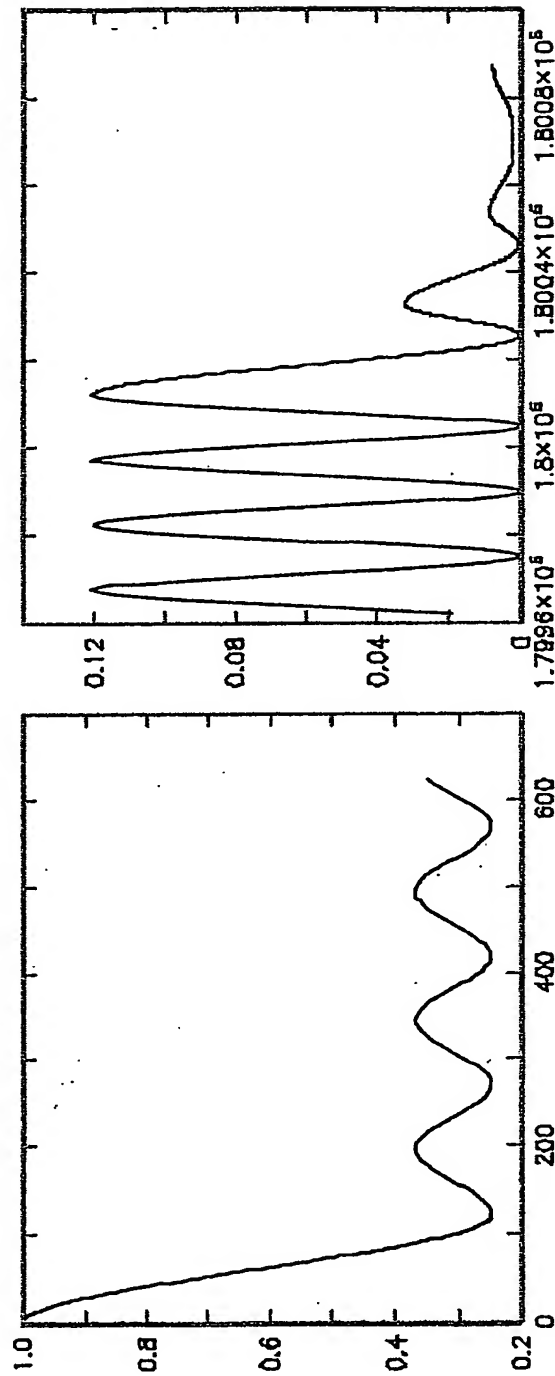
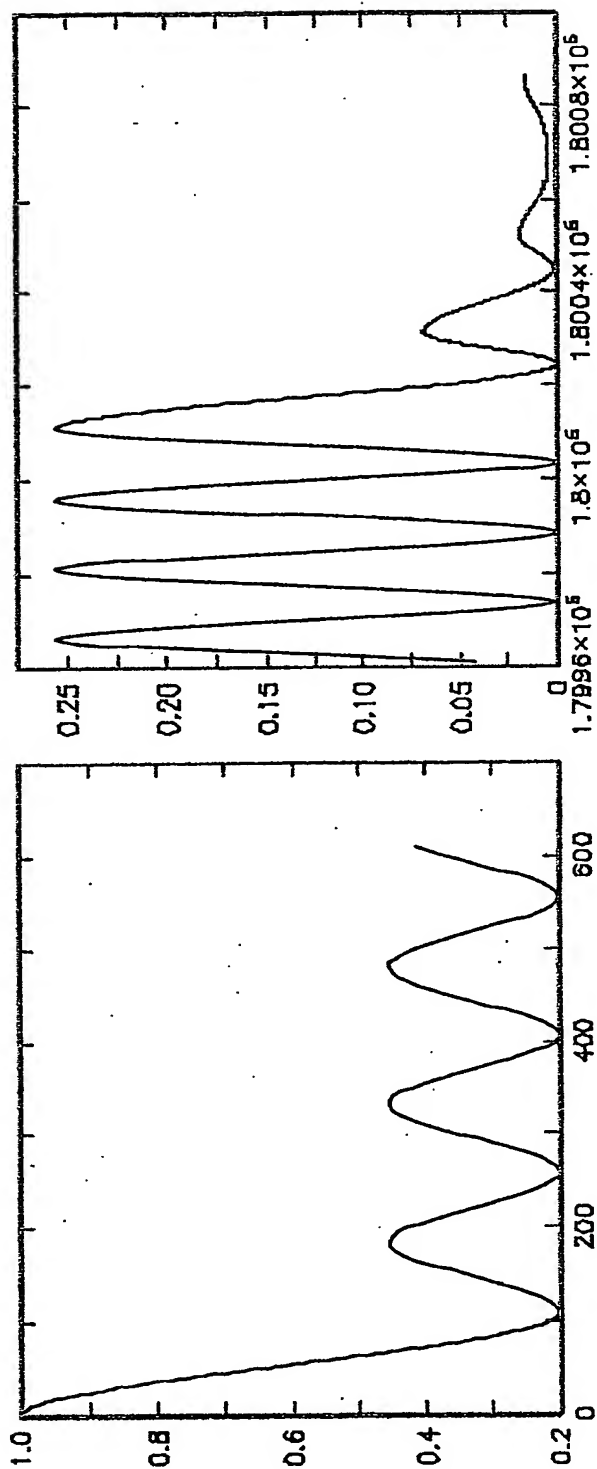


Fig. 5

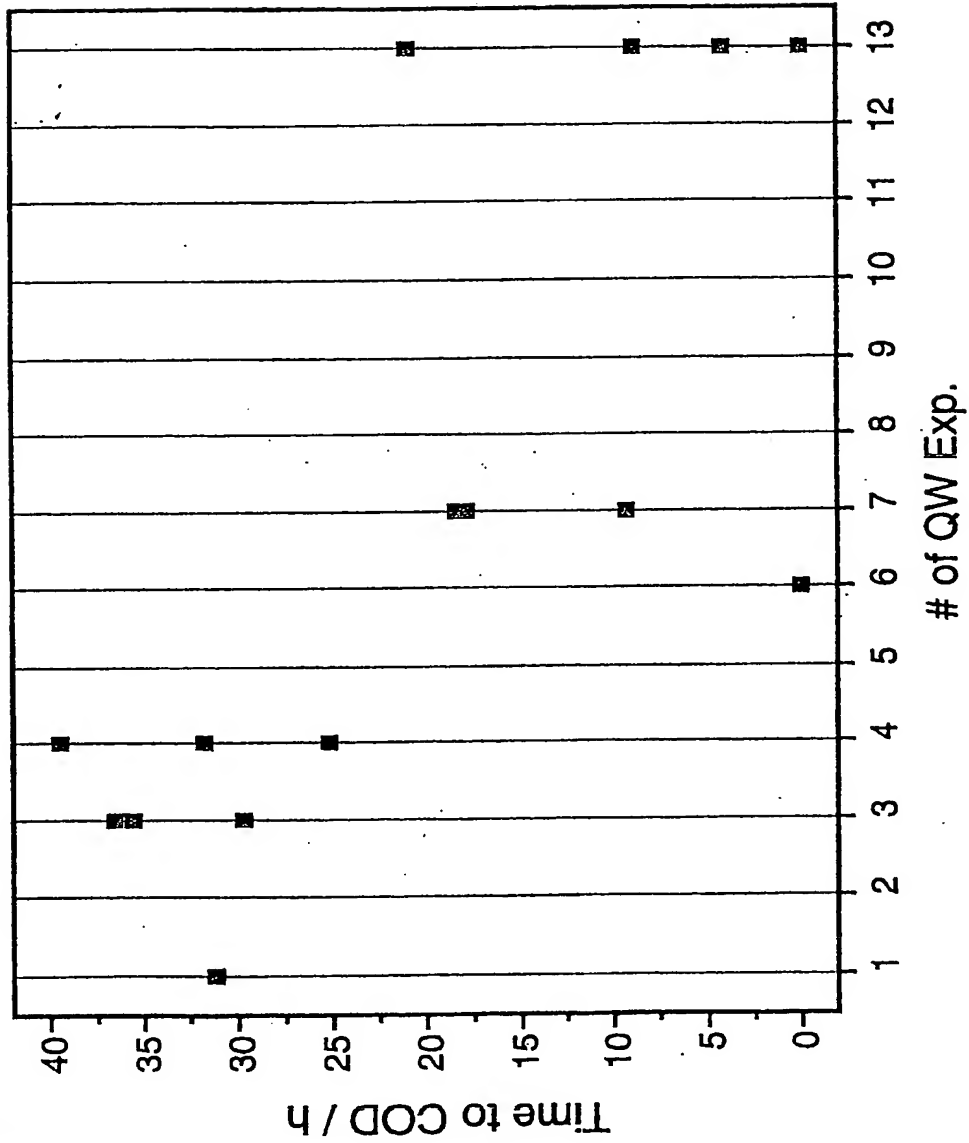


Phase Shifting Quarter Wave Coating with a 1 % Reflectance

Fig. 6



Phase Shifting Quarter Wave Coating with a 4 % Reflectance



Time to COD vs. # of QW Exp

Fig. 7

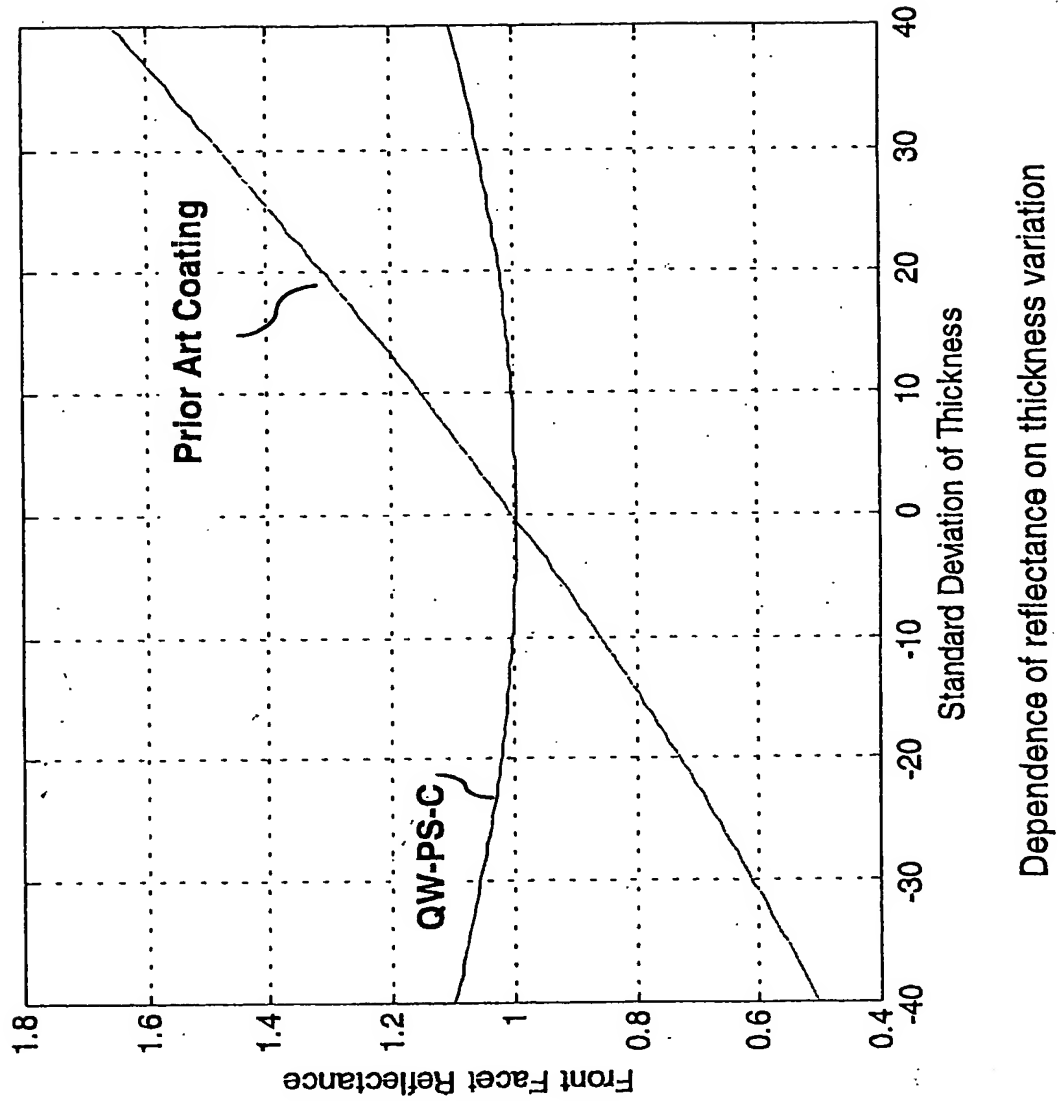
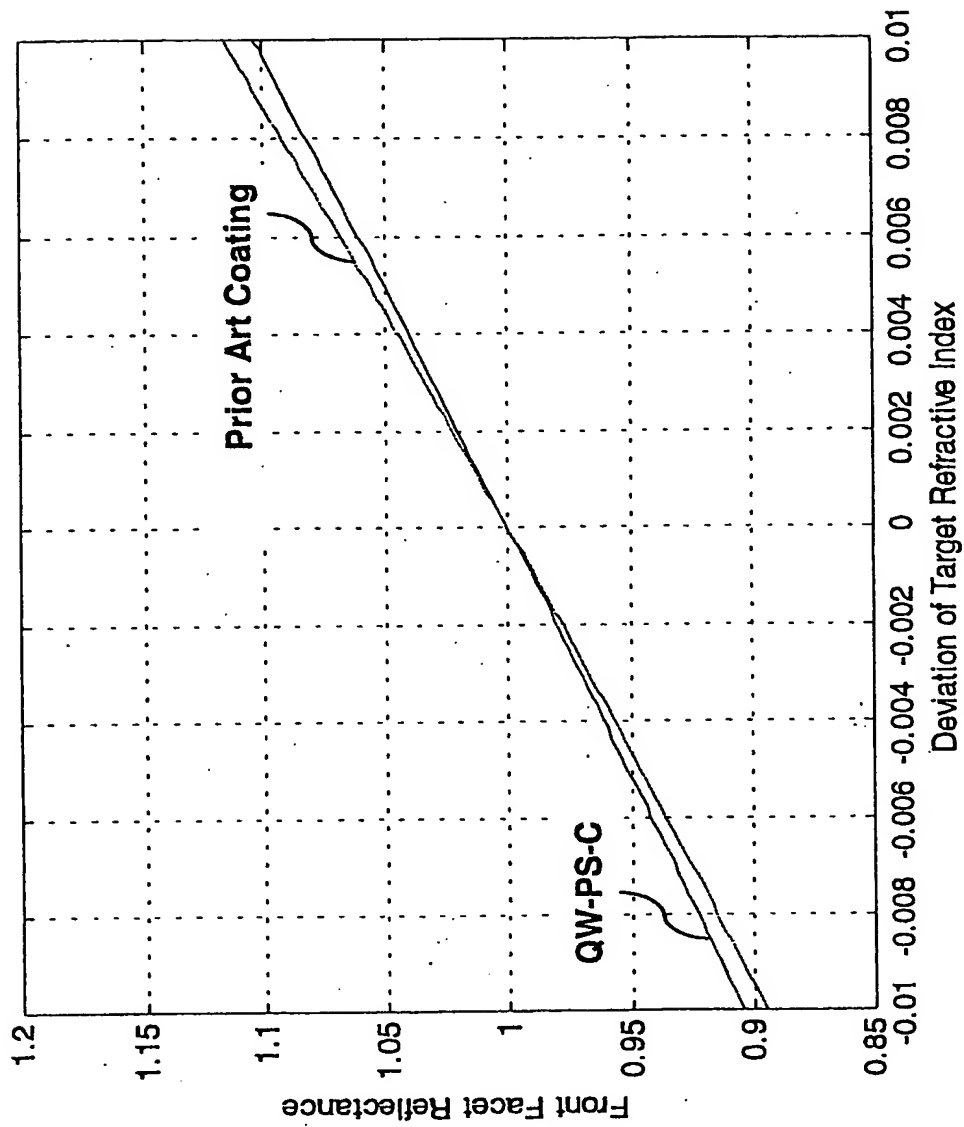




Fig. 9



Dependence of Reflectance on index variation

Fig. 10

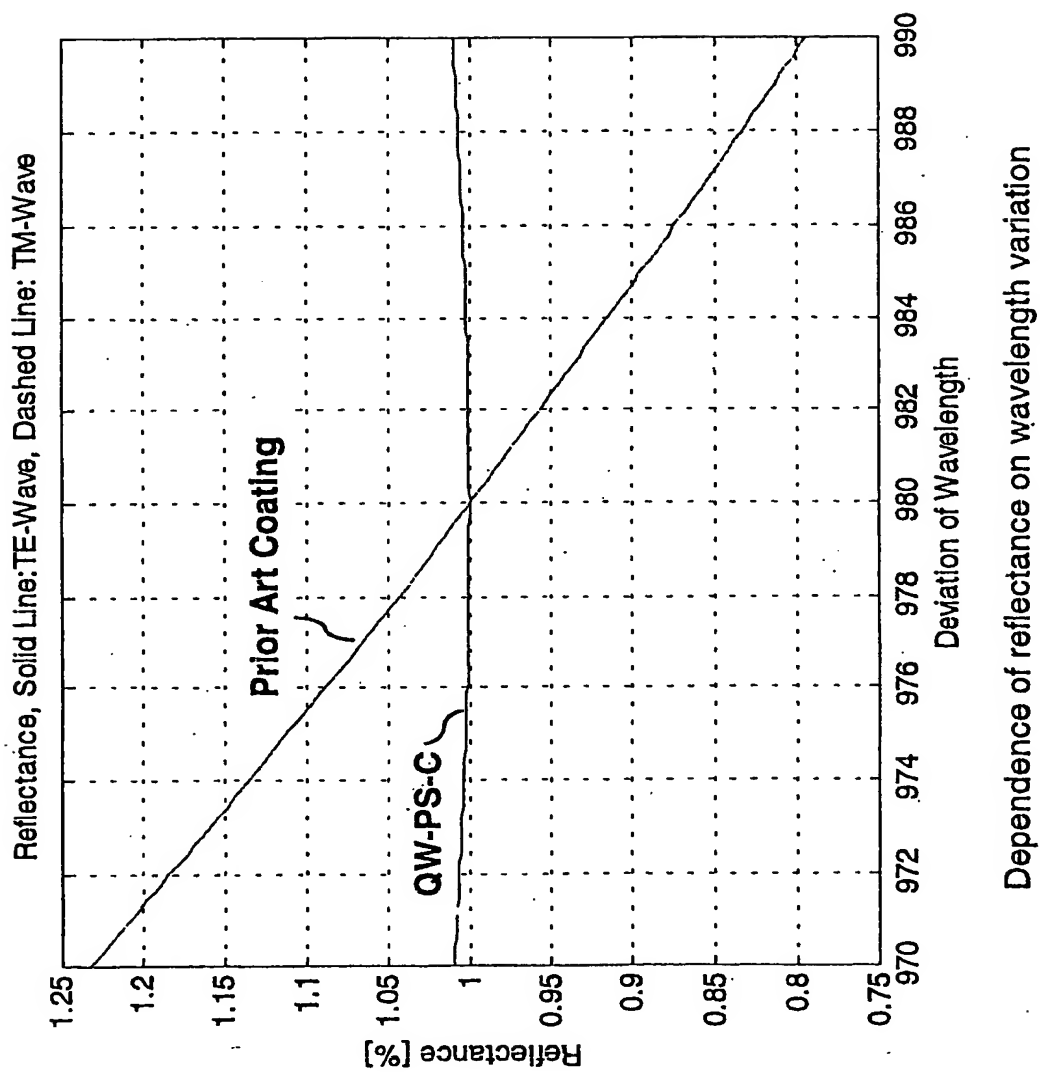


Fig. 11

**Process parameters**

Reflectivity $R$	index of refraction $n$	Substrate Temperature $T_s$ (°C)	Pressure $P$ (Torr)	Plasma Power $L_{\text{plasma}}$ (W)	nitrogen flux $n_{N_2}$ (sccm)	ammonia flux $n_{NH_3}$ (sccm)	silane flux(*) $n_{SiH_4}$ (sccm)
0.05%	1.86	300	1.4	25	35	18	236
1%	2.01	300	1.4	25	35	13	403
4%	2.23	300	1.4	25	35	8.5	491
1%(**)	1.83	300	1.4	20	330	11.2	300

(\*) precursor gas of 2% SiH<sub>4</sub> diluted in Helium

(\*\*) conventional non- $\lambda/4$  coating

Fig. 12

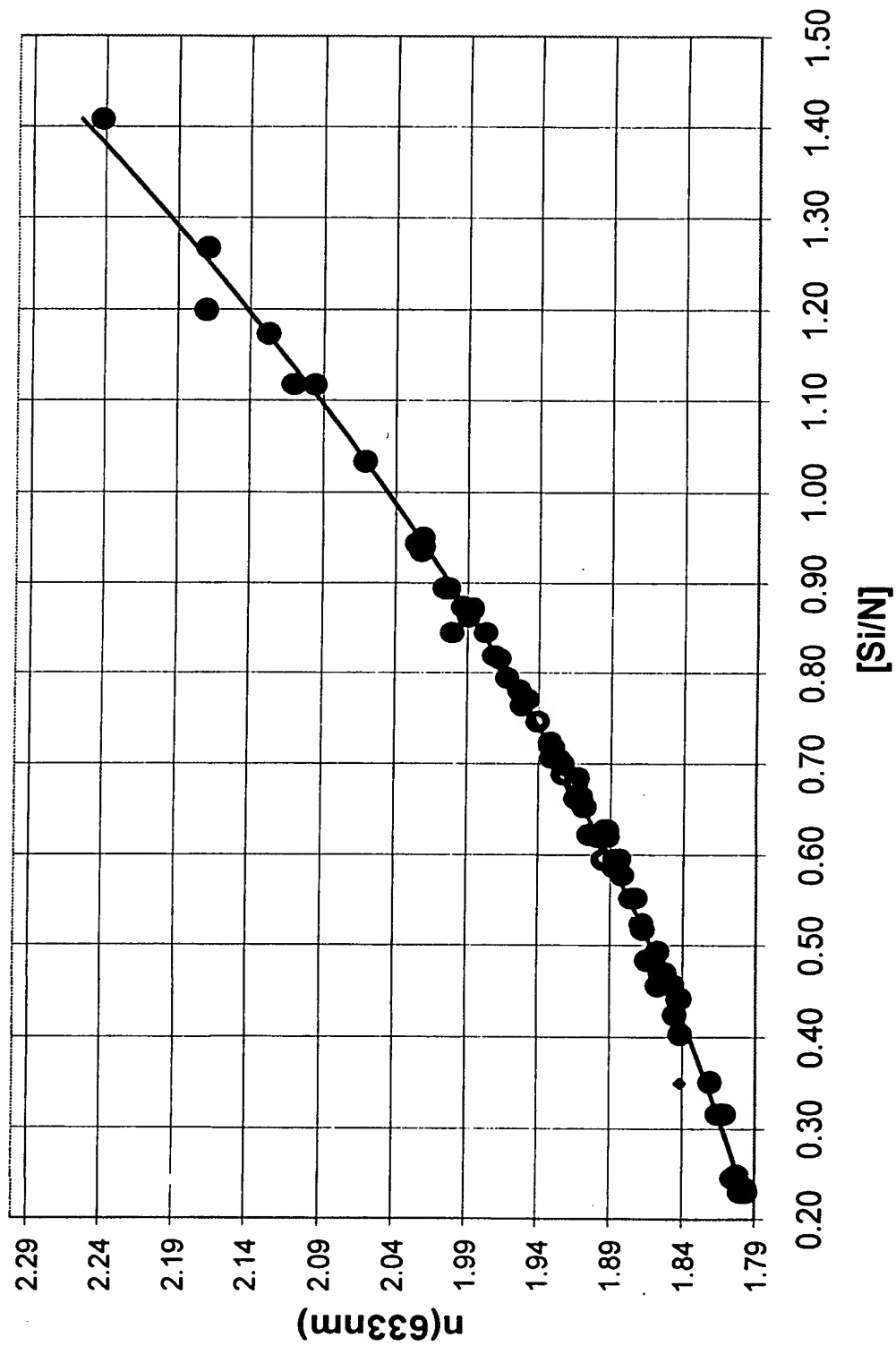


Fig. 13

